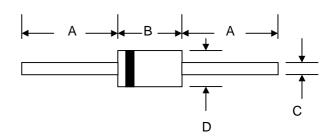


1N5820 - 1N5822

3.0A SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical Data

Case: Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

Polarity: Cathode Band

Weight: 1.2 grams (approx.)

Mounting Position: Any

Marking: Type Number

DO-201AD					
Dim	Min	Max			
Α	25.4	_			
В	8.50	9.50			
С	1.20	1.30			
D	5.0	5.60			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	1N5820	1N5821	1N5822	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		VRRM VRWM VR	20	30	40	V
RMS Reverse Voltage		VR(RMS)	14	21	28	V
Average Rectified Output Current (Note 1) $@T_L = 90^{\circ}C$		lo	3.0			Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) @T _L = 75°C		lfsm	80			А
Forward Voltage	@I _F = 3.0A @I _F = 9.4A	VFM	0.475 0.850	0.50 0.90	0.525 0.950	V
Peak Reverse Current At Rated DC Blocking Voltage	@T _A = 25°C @T _A = 100°C	lкм	2.0 20			mA
Typical Junction Capacitance (Note 2)		Cj	250			pF
Typical Thermal Resistance Junction to Ambient		$R_{ heta}JA$	20			K/W
Operating and Storage Temperature Range		Тj, Тsтg	-65 to +150			°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

